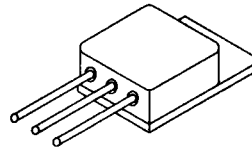
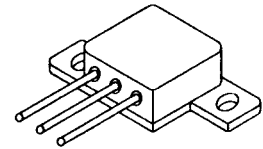




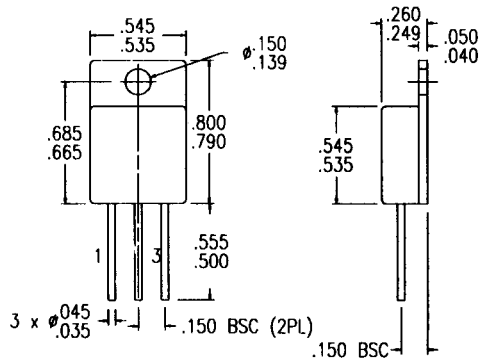
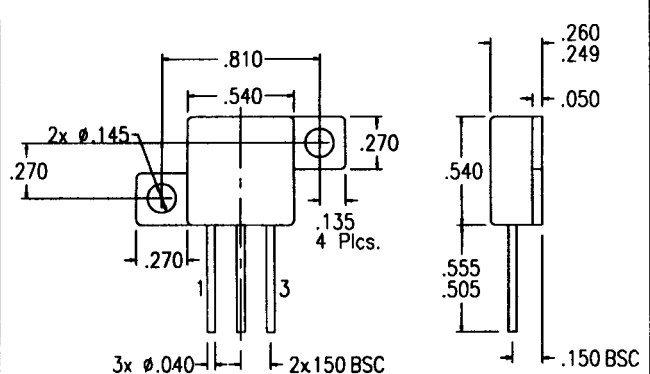
PRELIMINARY

SOLID STATE DEVICES, INC14849 Firestone Boulevard · La Mirada, CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424**Designer's Data Sheet****FEATURES:**

- Rugged construction with polysilicon gate
- Low RDS(on) and high transconductance
- Excellent high temperature stability
- Very fast switching speed
- Fast recovery and superior dv/dt performance
- Increased reverse energy capability
- Low input and transfer capacitance for easy paralleling
- Ceramic Seals for improved hermeticity
- Hermetically sealed surface mount power package
- TX, TXV and Space Level screening available
- Replaces: IXTH20N60 Types

SFF20N60M
SFF20N60Z**20 AMPS**
600 VOLTS
0.40 Ω
N-CHANNEL
POWER MOSFET**TO-254****TO-254Z****MAXIMUM RATINGS**

CHARACTERISTIC	SYMBOL	VALUE	UNIT
Drain to Source Voltage	V _{DS}	600	Volts
Gate to Source Voltage	V _{GS}	±20	Volts
Continuous Drain Current	I _D	20	Amps
Operating and Storage Temperature	T _{OP} & T _{STG}	-55 to +175	°C
Thermal Resistance, Junction to Case	R _{θJC}	0.83	°C/W
Total Device Dissipation @ TC=25°C Total Device Dissipation @ TC=55°C	P _D	150 114	Watts

PACKAGE OUTLINE: TO-254PIN OUT:
PIN 1: DRAIN
PIN 2: SOURCE
PIN 3: GATE**PACKAGE OUTLINE: TO-254Z**PIN OUT:
PIN 1: DRAIN
PIN 2: SOURCE
PIN 3: GATE

Available with Glass or Ceramic Seals. Contact Factory for details.

NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.**DATA SHEET #: F00201 B****MED**

SFF20N60M SFF20N60Z

PRELIMINARY



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ELECTRICAL CHARACTERISTICS @ T_J=25 °C (Unless Otherwise Specified)

RATING	SYMBOL	MIN	TYP	MAX	UNIT
Drain to Source Breakdown Voltage (V _{GS} =0 V, I _D =250μA)	BV _{DSS}	600	---	---	V
Drain to Source on State Resistance (V _{GS} =10 V, I _D =60% Rated ID)	R _{DS(on)}	---	0.35	0.40	Ω
On State Drain Current (V _{DS} > I _{D(on)} X R _{DS(on)} Max, V _{GS} =10 V)	I _{D(on)}	20	---	---	A
Gate Threshold Voltage (V _{DS} =V _{GS} , I _D =250μA)	V _{GS(th)}	2.0	---	4.5	V
Forward Transconductance (V _{DS} > I _{D(on)} X R _{DS(on)} Max, I _{DS} =60% rated ID)	g _{fs}	12	18	---	S(Ω)
Zero Gate Voltage Drain Current (V _{DS} =max rated voltage, V _{GS} =0 V) (V _{DS} =80% rated V _{DS} , V _{GS} =0 V, T _A =125°C)	I _{DSS}	---	---	200 1000	μA
Gate to Source Leakage Forward Gate to Source Leakage Reverse	At rated V _{GS} I _{GSS}	---	---	+100 -100	nA
Total Gate Charge Gate to Source Charge Gate to Drain Charge	V _{GS} =10 Volts 80% rated V _{DS} 50 %Rated ID Q _g Q _{gs} Q _{gd}	---	150 29 60	170 40 85	nC
Turn on Delay Time Rise Time Turn Off Delay Time Fall Time	V _{DD} =50% rated V _{DS} 50% rated ID R _G =6.2Ω t _{d(on)} t _r t _{d(off)} t _f	---	30 30 110 30	40 60 150 60	nsec
Diode Forward Voltage (I _S =rated ID, V _{GS} =0 V, T _J =25°C)	V _{SD}	---	---	1.5	V
Diode Reverse Recovery Time Reverse Recovery Charge	T _J =25°C I _F =10A di/dt=100 A/μsec t _{rr} Q _{RR}	---	---	800 ---	nsec μC
Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{GS} =0 Volts V _{DS} =25 Volts f= 1 MHz C _{iss} C _{oss} C _{rss}	---	4500 420 140	---	pF

SAFE OPERATING AREA (S.O.A.)
T_C = 25 °C, D.C. CONDITION

